Unit: mm

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

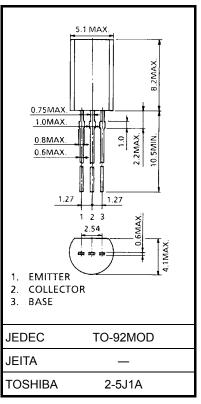
2SA1680

Power Amplifier Applications
Power Switching Applications

- Low collector-emitter saturation voltage: VCE (sat) = -0.5 V (max)(IC = -1 A)
- High collector power dissipation: $P_C = 900 \text{ mW} \text{ (Ta} = 25 \text{ °C)}$
- High-speed switching: $t_{stg} = 300 \text{ ns (typ.)}$
- Complementary to 2SC4408.

Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | Symbol | Rating | Unit |
|-----------------------------|------------------|------------|------|
| Collector-base voltage | V_{CBO} | -60 | V |
| Collector-emitter voltage | V _{CEO} | -50 | V |
| Emitter-base voltage | V _{EBO} | -6 | V |
| Collector current | IC | -2 | Α |
| Base current | ΙΒ | -0.2 | Α |
| Collector power dissipation | PC | 900 | mW |
| Junction temperature | Tj | 150 | °C |
| Storage temperature range | T _{stg} | -55 to 150 | °C |



Weight: 0.36 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high

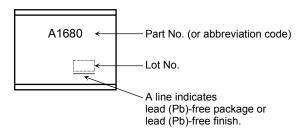
temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

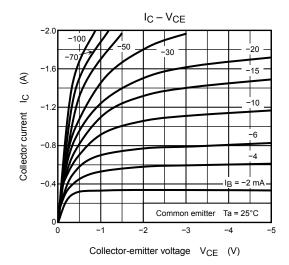
Electrical Characteristics (Ta = 25°C)

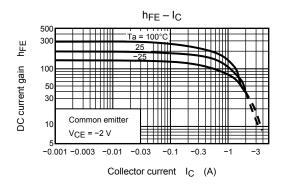
| Chara | acteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|------------------------------|--------------------|-----------------------|---|-----|------|------|------|
| Collector cut-off c | urrent | I _{CBO} | V _{CB} = -60 V, I _E = 0 | _ | _ | -1.0 | μΑ |
| Emitter cut-off cur | rrent | I _{EBO} | V _{EB} = -6 V, I _C = 0 | _ | _ | -1.0 | μΑ |
| Collector-emitter | breakdown voltage | V (BR) CEO | I _C = -10 mA, I _B = 0 | -50 | _ | _ | V |
| DC current gain | | h _{FE (1)} | V _{CE} = -2 V, I _C = -100 mA | 120 | _ | 400 | |
| | | h _{FE (2)} | V _{CE} = -2 V, I _C = -1.5 A | 40 | _ | _ | |
| Collector-emitter | saturation voltage | V _{CE} (sat) | I _C = -1 A, I _B = -0.05 A | _ | _ | -0.5 | V |
| Base-emitter satu | ration voltage | V _{BE (sat)} | I _C = -1 A, I _B = -0.05 A | _ | _ | -1.2 | V |
| Transition frequer | псу | f _T | V _{CE} = -2 V, I _C = -100 mA | _ | 100 | _ | MHz |
| Collector output capacitance | | C _{ob} | V _{CB} = -10 V, I _E = 0, f = 1 MHz | _ | 23 | _ | pF |
| Switching time Sto | Turn-on time | ton | Output 20 μ s Input $\stackrel{B2}{\longrightarrow}$ $\stackrel{C}{\longrightarrow}$ | _ | 0.1 | _ | |
| | Storage time | t _{stg} | | _ | 0.3 | _ | μs |
| | Fall time | t _f | | _ | 0.1 | _ | |

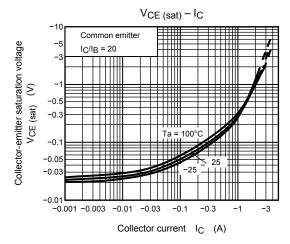
Marking

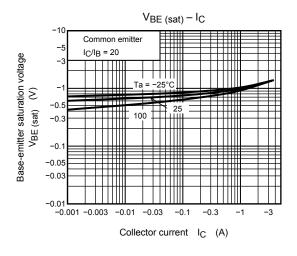


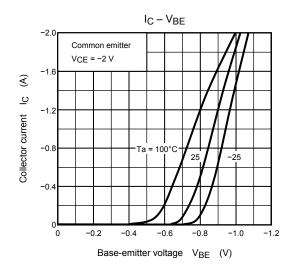
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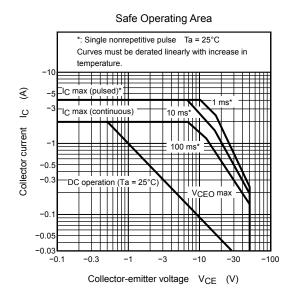












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20070701-EN

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